

SAMYANG ELECTRONICS MBRF2020 --- MBRF20200

SCHOTTKY BARRIER RECTIFIER

FEATURES

- \bigotimes Metal-semiconductor junction with guard ring
- \bigcirc Epitaxial construction
- $\bigcirc \mathsf{Low}$ forward voltage drop, low switching losses
- \bigcirc High surge capability
- ◇ For use in low voltage, high frequency inverters free wheeling, and polarity protection applications

MECHANICAL DATA

- ♦ Case: JEDEC ITO-220AC, molded plastic
- - MIL-STD-750,Method 2026
- ◇Polarity: As marked
- ♦ Weight: 0.08ounces, 2.24 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

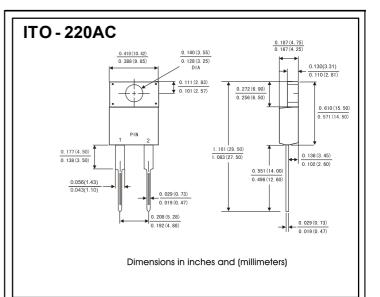
	Symbols	MBRF 2020	MBRF 2030	MBRF 2040	MBRF 2050	MBRF 2060	MBRF 2080	MBRF 20A0	MBRF 20150	MBRF 20200	Units
Maximum repetitive peak reverse voltage	Vrrm	20	30	40	50	60	80	100	150	200	Volts
Maximum RMS voltage	Vrms	14	21	28	35	42	56	70	105	140	Volts
Maximum DC blocking voltage	Vdc	20	30	40	50	60	80	100	150	200	Volts
Maximum average forward rectified current See Fig. 1	I(AV)	20.0							Amps		
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	IFSM	200.0									Amps
Maximum instantaneous forward voltage at 20.0 A	VF	0.60			0.3	75	0.85		0. 90	0. 95	Volts
Maximum instantaneous reverse T _c =25°C		0.2									•
current at rated DC blocking voltage(Note 1) T _c = 125°C	R	30			50						A
Typical thermal resistance (Note 2)	R_{θ} JC	3.0									°C/W
Operating junction temperature range	TJ	-65 to+150									°C
Storage temperature range	Tsig	-65 to+150									°C

NOTE: 1. Pulse test: 300us pulse width, 1% duty cycle.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

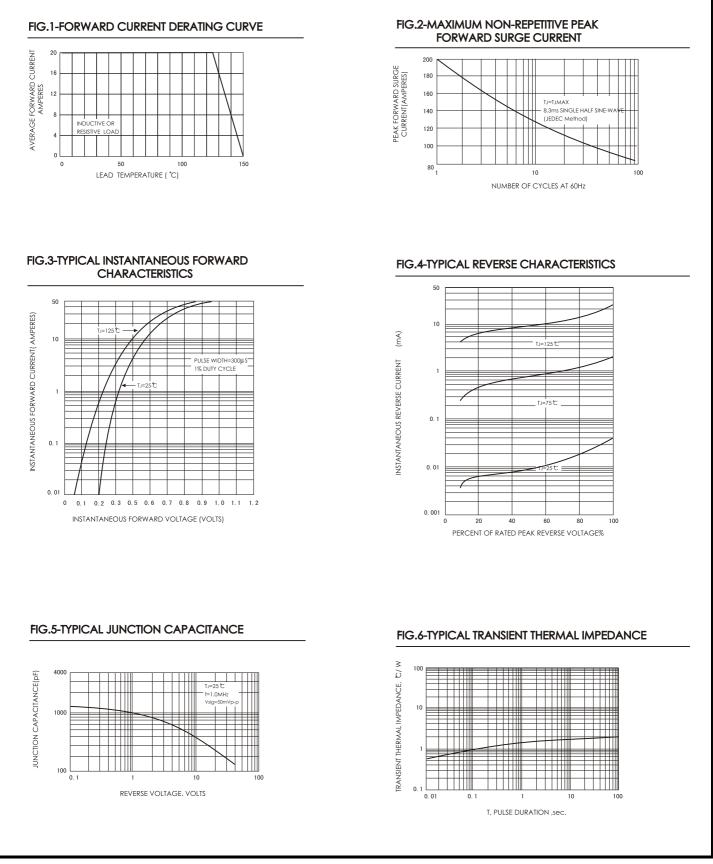
3. Thermal resistance junction to ambient

VOLTAGE RANGE: 20 --- 200 V CURRENT: 20.0A



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RATINGS AND CHARACTERISTIC CURVES



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